

November 2013

FQB7P20

P-Channel QFET® MOSFET

-200 V, -7.3 A, 690 mΩ

Description

This P-Channel enhancement mode power MOSFET is \bullet -7.3 A, -200 V, $R_{DS(on)}$ = 690 m Ω (Max.) @ V_{GS} = -10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state

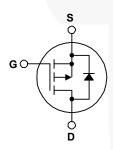
Low Gate Charge (Typ. 19 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 25 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_D = -3.65 A$

- · RoHS Compliant





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQB7P20TM	Unit
V_{DSS}	Drain-Source Voltage		-200	V
I _D	Drain Current - Continuous (T _C = 25°C)		-7.3	Α
	- Continuous (T _C = 100°C)		-4.6	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	-29.2	Α
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	570	mJ
I _{AR}	Avalanche Current	(Note 1)	-7.3	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	9.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3		-5.5	V/ns
P _D	Power Dissipation (T _A = 25°C) *		3.13	W
	Power Dissipation (T _C = 25°C)		90	W
	- Derate above 25°C		0.72	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _I	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.		300	°C
'L			300	C

Thermal Characteristics

Symbol	Parameter	FQB7P20TM	Unit
R_{\thetaJC}	Thermal Resistance, Junction to Case, Max.	0.7	
В	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
ØÛÓÏ ÚŒVT	FQB7P20	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics

Symbol	Parameter	Test Conditions	Minž	Typž	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = -250 μA				V
ΔBV _{DSS} / ΔT	Breakdown Voltage Temperature Coefficient	I _D = -250 μA, Referenced to 25°C		-0.1		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -200 V, V _{GS} = 0 V			-1	μΑ
		V _{DS} = -160 V, T _C = 125°C			-10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-3.0		-5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -3.65 A		0.54	0.69	Ω
9 _{FS}	Forward Transconductance	V _{DS} = -40 V, I _D = -3.65 A		4.4		S
Dynam	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$	\	590	770	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		140	180	pF
C _{rss}	Reverse Transfer Capacitance			25	35	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V = 100 V L = 7.2 A		15	40	ns
t _r	Turn-On Rise Time	$V_{DD} = -100 \text{ V}, I_{D} = -7.3 \text{ A},$ $R_{G} = 25 \Omega$		110	230	ns
t _{d(off)}	Turn-Off Delay Time	1(G - 23 sz		30	70	ns
t _f	Turn-Off Fall Time	(Note 4)		42	90	ns
Qg	Total Gate Charge	V _{DS} = -160V, I _D = -7.3 A,		19	25	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V		4.6		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	/	9.5		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
Is	Maximum Continuous Drain-Source Diode Forward Current				-7.3	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				-29.2	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -7.3 \text{ A}$			-5.0	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = -7.3 A,		180		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		1.07		μC

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = 16 mH, I_{AS} = -7.3 A, V_{DD} = -50 V, R_{G} = 25 Ω , starting T_{J} = 25°C. 3. I_{SD} ≤ -7.3 A, di/dt ≤ 300 A/ μ s , V_{DD} ≤ BV $_{DSS}$, starting T_{J} = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

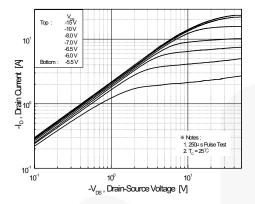


Figure 1. On-Region Characteristics

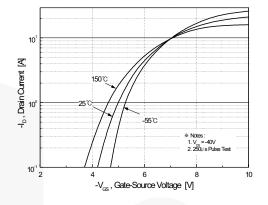


Figure 2. Transfer Characteristics

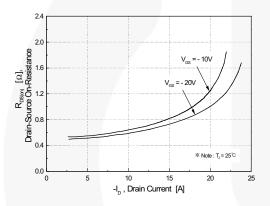


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

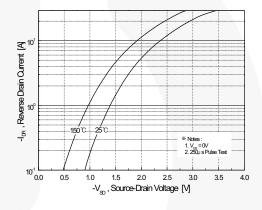


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

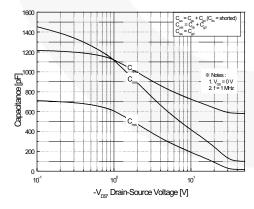


Figure 5. Capacitance Characteristics

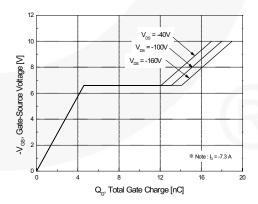


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

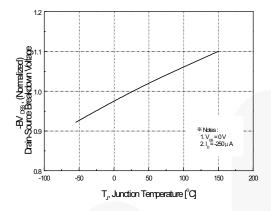


Figure 7. Breakdown Voltage Variation vs. Temperature

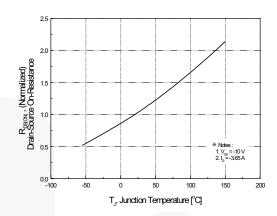


Figure 8. On-Resistance Variation vs. Temperature

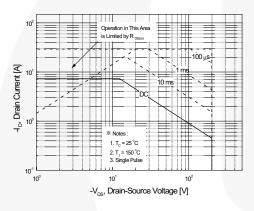


Figure 9. Maximum Safe Operating Area

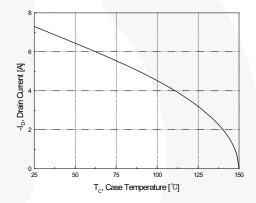


Figure 10. Maximum Drain Current vs. Case Temperature

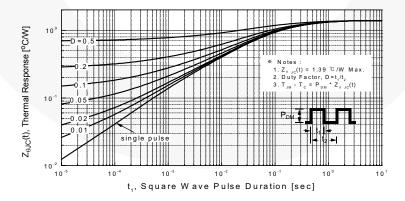


Figure 11. Transient Thermal Response Curve

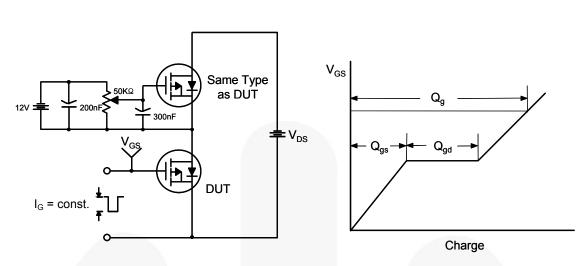


Figure 12. Gate Charge Test Circuit & Waveform

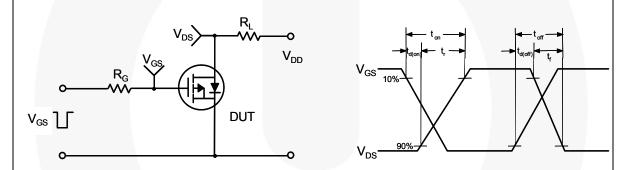


Figure 13. Resistive Switching Test Circuit & Waveforms

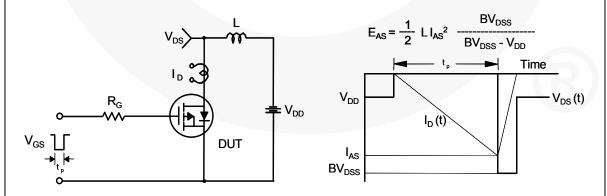
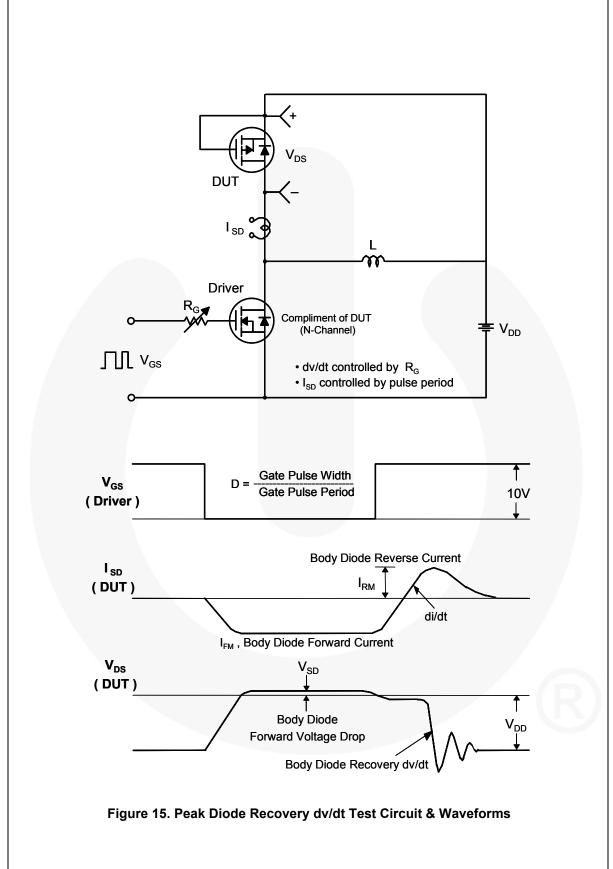


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

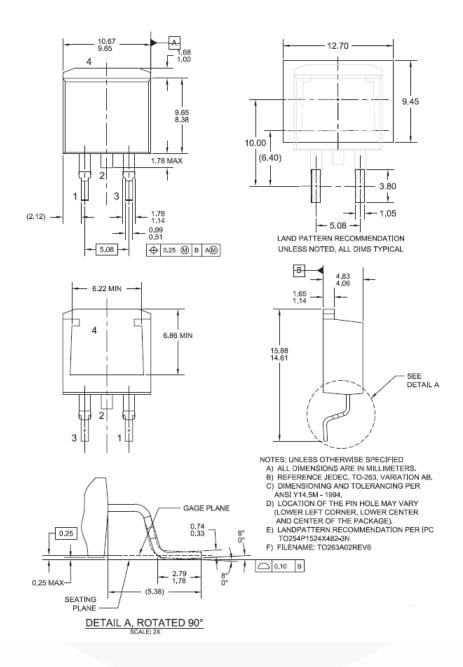


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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